

**TYPE
NAME**

ML60116R , ML64116R

DESCRIPTION

ML6XX16 is a high power AlGaAs semiconductor laser which provides a stable, single transverse mode oscillation with emission wavelength of 785nm and standard light output of 30mW.

ML6XX16 is produced by the MOCVD crystal growth method which is excellent in mass production and characteristics uniformity. This is a high -performance, highly reliable, and long life semiconductor laser.

FEATURES

- Output 30mW (CW) 40mW (pulse)
- Short astigmatic distance
- MQW * active layer
* : Multiple Quantum Well
- Built-in monitor photodiode

APPLICATION

Optical disc drive (rewritable , write once)

ABSOLUTE MAXIMUM RATINGS (Note 1)

Symbol	Parameter	Conditions	Ratings	Unit
Po	Light output power	CW	40	mW
		Pulse(Note 2)	50	
VRL	Reverse voltage (laser diode)	-	2	V
VRD	Reverse voltage (Photodiode)	-	30	V
IFD	Forward current (Photodiode)	-	10	mA
Tc	Case temperature	-	-40 ~ +60	°C
Tstg	Storage temperature	-	-55 ~ +100	°C

Note1: The maximum rating means the limitation over which the laser should not be operated even instant time, and this does not mean the guarantee of its lifetime.As for the reliability,please refer to the reliability report from Mitsubishi Semiconductor Quality Assurance Department.

Note2: TARGET SPEC /Condition Duty less than 50%,pulse width less than 1ms

ELECTRICAL/OPTICAL CHARACTERISTICS (Case temperature Tc=25°C)


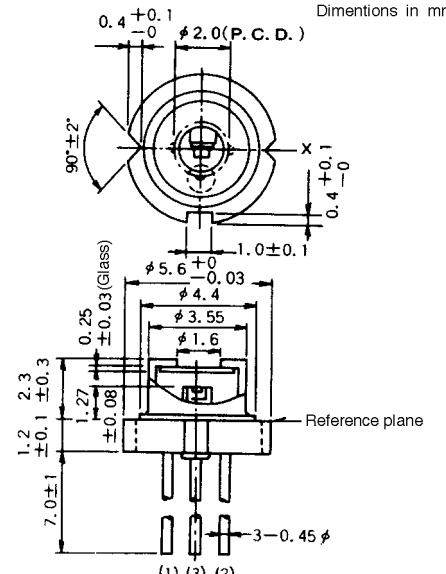
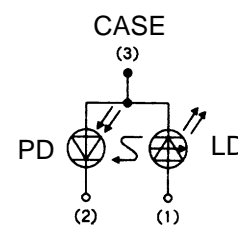
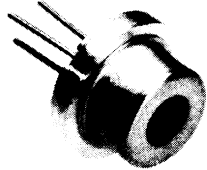
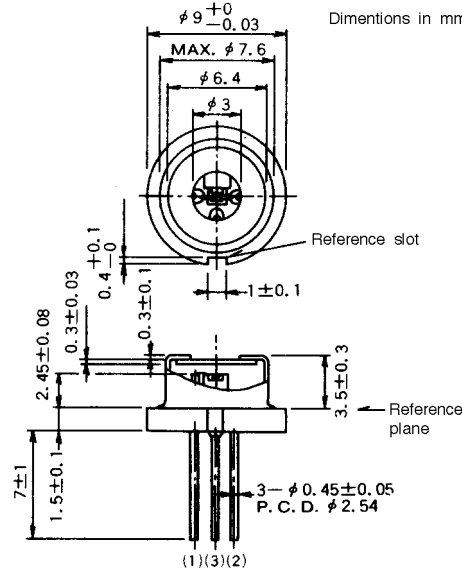
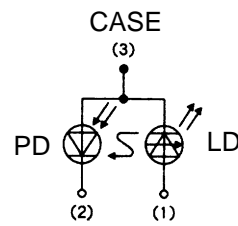
Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I _{th}	Threshold current	CW	-	30	50	mA
I _{op}	Operation current	CW,Po=30mW	-	80	110	mA
η	Slope efficiency	CW,Po=30mW	0.40	0.55	0.75	mW/mA
V _{op}	Operating voltage	CW,Po=30mW		2.0	2.5	V
λ _p	Peak wavelength	CW,Po=30mW	770	785	800	nm
θ _{//}	Beam divergence angle (parallel)	CW,Po=30mW	8	10	13	°
θ _⊥	Beam divergence angle (perpendicular)	CW,Po=30mW	22	25	28	°
I _m	Monitoring output current (Photodiode)	CW,Po=30mW,VRD=1V RL=10Ω (Note 4)	-	0.2	-	mA
I _m (Note 3)			-	0.5	-	
I _D	Dark current (Photodiode)	VRD=10V	-	-	0.5	uA
C _t	Capacitance (Photodiode)	VRD=5V	-	7	-	pF

Note 3: Applicable to ML64116R

Note 4: RL=the load resistance of photodiode

MITSUBISHI LASER DIODES
ML6XX16 SERIES
 FOR OPTICAL INFORMATION SYSTEMS

OUTLINE DRAWINGS

<p>ML60116R</p> 	<p>Dimensions in mm</p>  <p>0.4 $\begin{smallmatrix} +0.1 \\ -0 \end{smallmatrix}$ $\phi 2.0$ (P. C. D.)</p> <p>90° ± 2'</p> <p>0.4 $\begin{smallmatrix} +0.1 \\ -0 \end{smallmatrix}$</p> <p>1.0 ± 0.1</p> <p>$\phi 5.6$ $\begin{smallmatrix} +0 \\ -0.03 \end{smallmatrix}$</p> <p>$\phi 4.4$</p> <p>$\phi 3.55$</p> <p>$\phi 1.6$</p> <p>0.25 ± 0.03 (Glass)</p> <p>1.27 ± 0.08</p> <p>1.2 ± 0.1</p> <p>2.3 ± 0.3</p> <p>7.0 ± 1</p> <p>Reference plane</p> <p>3 - $\phi 0.45$</p> <p>(1) (3) (2)</p>	<p>CASE (3)</p>  <p>PD</p> <p>S</p> <p>LD</p> <p>(2) (1)</p>
<p>ML64116R</p> 	<p>Dimensions in mm</p>  <p>$\phi 9$ $\begin{smallmatrix} +0 \\ -0.03 \end{smallmatrix}$</p> <p>MAX. $\phi 7.6$</p> <p>$\phi 6.4$</p> <p>$\phi 3$</p> <p>Reference slot</p> <p>0.4 $\begin{smallmatrix} +0.1 \\ -0 \end{smallmatrix}$</p> <p>0.3 ± 0.03</p> <p>0.3 ± 0.1</p> <p>1 ± 0.1</p> <p>2.45 ± 0.08</p> <p>0.3 ± 0.03</p> <p>3.5 ± 0.3</p> <p>Reference plane</p> <p>7 ± 1</p> <p>1.5 ± 0.1</p> <p>3 - $\phi 0.45 \pm 0.05$</p> <p>P. C. D. $\phi 2.54$</p> <p>(1) (3) (2)</p>	<p>CASE (3)</p>  <p>PD</p> <p>S</p> <p>LD</p> <p>(2) (1)</p>